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20 V, single P-channel Trench MOSFET 1 August 2012

Product data sheet

1. Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- 1.8 kV ESD protected

1.3 Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quid	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V_{GS} = -4.5 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-1.4	А
Static characteristics							
$R_{DSon} \qquad drain-source on-state resistance \qquad V_{GS} = -4.5 V; I_D = -0.3 A; T_j = 25 °C \qquad - 330 450 m\Omega$					mΩ		

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².





20 V, single P-channel Trench MOSFET

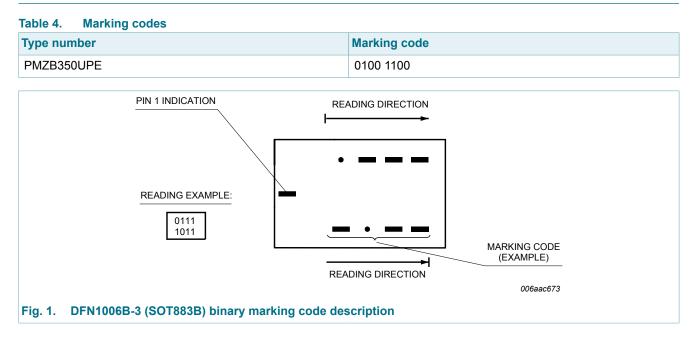
2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D
2	S	source		
3	D	drain	Transparent top view DFN1006B-3 (SOT883B)	G S 017aaa259

3. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
PMZB350UPE	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

4. Marking



20 V, single P-channel Trench MOSFET

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-1.4	А
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-1	А
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-0.7	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-2.8	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T _{sp} = 25 °C		-	3125	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode	1				
I _S	source current	T _{amb} = 25 °C	[1]	-	-0.8	А
ESD maxim	num rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	1800	V

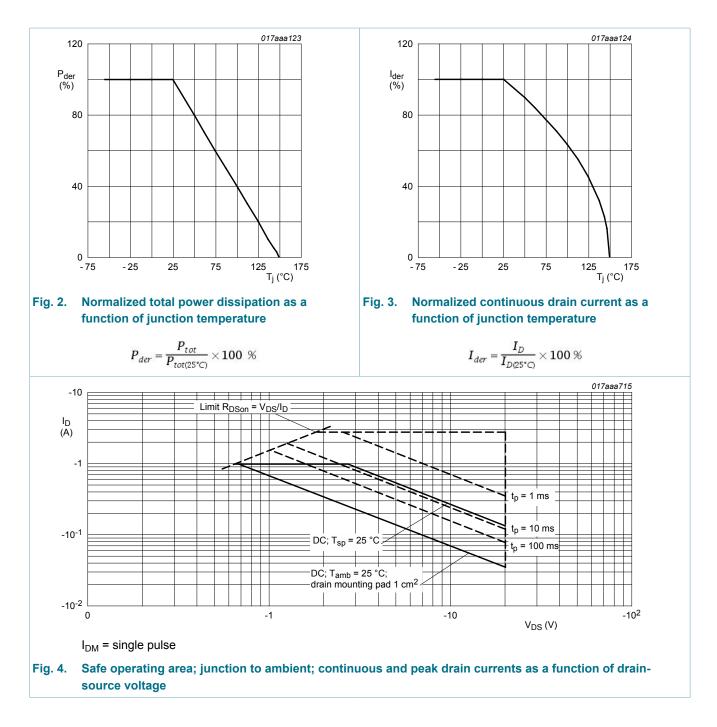
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.

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20 V, single P-channel Trench MOSFET



6. Thermal characteristics

Table 6. T	hermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to		in free air	[1]	-	304	350	K/W
	from junction to ambient		[2]	-	150	175	K/W
	ampient		[3]	-	90	103	K/W

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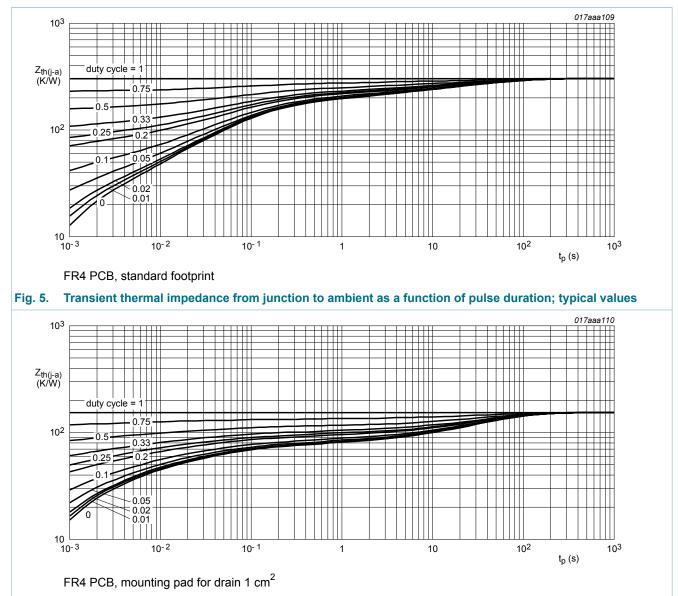
20 V, single P-channel Trench MOSFET

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	35	40	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm², $t \le 5$ s.



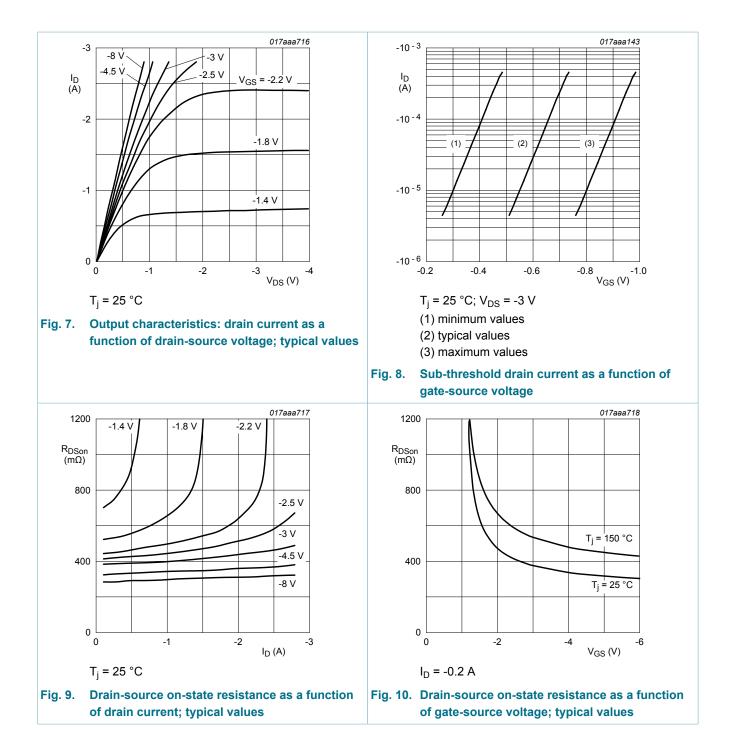


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7. Characteristics

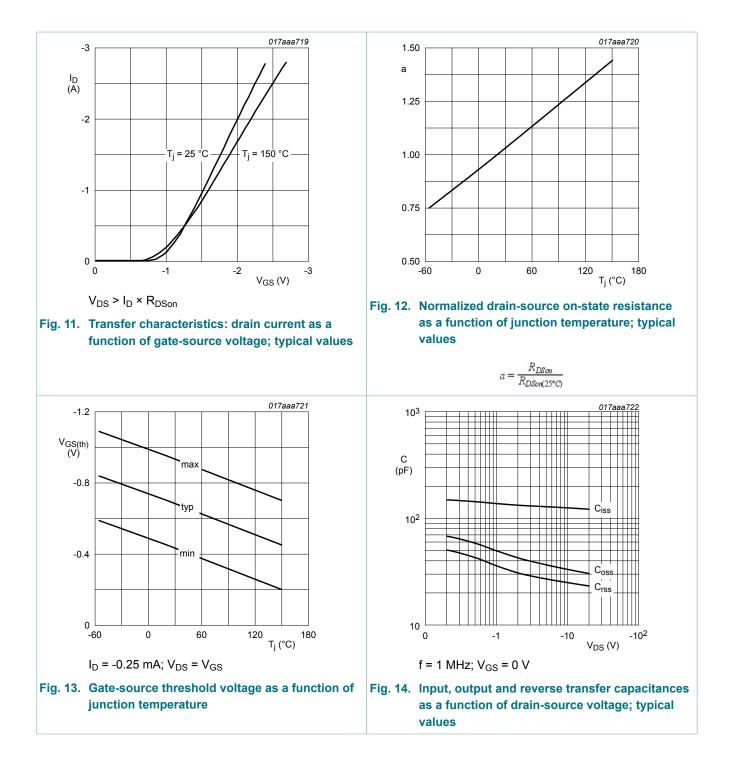
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{DS} = -20 V; V _{GS} = 0 V; T _j = 150 °C	-	-	-10	μA
I _{GSS}	gate leakage current	V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
R _{DSon} drain-source on-state resistance		V_{GS} = -4.5 V; I _D = -0.3 A; T _j = 25 °C	-	330	450	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -0.3 A; T _j = 150 °C	-	478	645	mΩ
	V _{GS} = -2.5 V; I _D = -0.2 A; T _j = 25 °C	-	420	645	mΩ	
		V _{GS} = -1.8 V; I _D = -0.1 A; T _j = 25 °C	-	520	940	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I _D = -0.3 A; T _j = 25 °C	-	1.4	-	S
Dynamic ch	aracteristics	· · · · · · · · · · · · · · · · · · ·				
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I _D = -0.3 A; V _{GS} = -4.5 V;	-	1.3	1.9	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.2	-	nC
Q _{GD}	gate-drain charge		-	0.25	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	127	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	34	-	pF
C _{rss}	reverse transfer capacitance		-	25	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I _D = -0.3 A; V _{GS} = -4.5 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	5	-	ns
t _{d(off)}	turn-off delay time		-	26	-	ns
t _f	fall time	1	-	9	-	ns
Source-dra	in diode	· · · · · · · · · · · · · · · · · · ·				
V _{SD}	source-drain voltage	I _S = -0.1 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.7	-1.2	V

20 V, single P-channel Trench MOSFET



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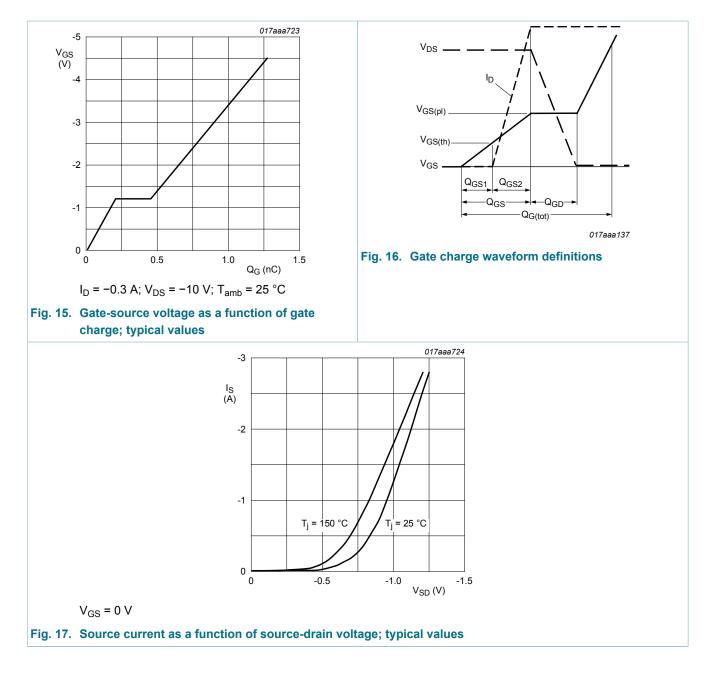
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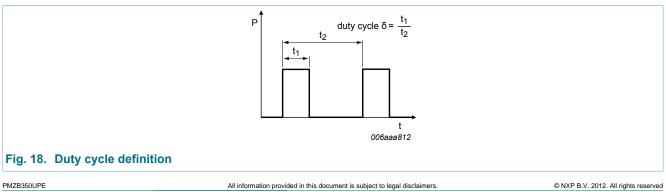
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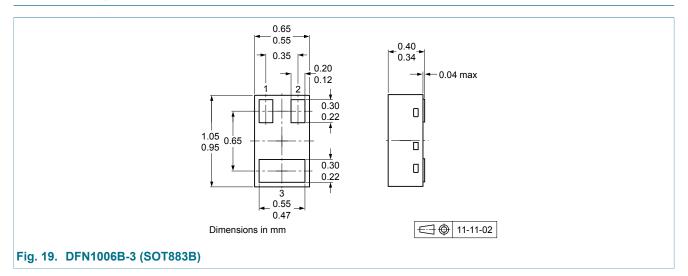


Test information 8.



20 V, single P-channel Trench MOSFET

9. Package outline



10. Soldering

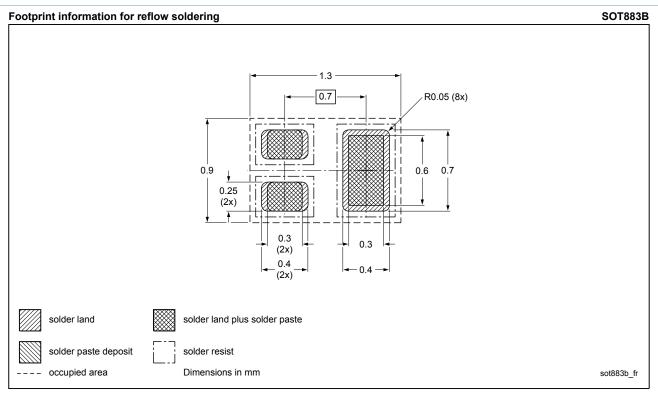


Fig. 20. Reflow soldering footprint for SOT883B (DFN1006B-3)

20 V, single P-channel Trench MOSFET

11. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMZB350UPE v.1	20120801	Product data sheet	-	-	

20 V, single P-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

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Document status [<u>1][2]</u>	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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